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| | Applicant(s): Hiroji EBE, et al. | |
| | Filing Date: September 16, 2003 | Group Art Unit: Not Yet Assigned |

U.S. PATENT DOCUMENTS

| Examiner Initial | Document No. | Name | Date | Class | Subclass | Filing Date (If appropriate) |
|---------------------|--------------|------|------|-------|----------|------------------------------------|
| _____ | AA | | | | | |
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| _____ | AD | | | | | |

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| | Document No. | Date | Country | Translation (Yes or No) | |
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| <u>DF</u> | AE | 9-326506 | 12/16/97 | Japan | Yes-Abstract/Discussed in the specification |
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| <u>DF</u> | AG | D. Leonard et al.; "Direct formation of quantum-sized dots from uniform coherent islands of InGaAs on GaAs surfaces"; <i>Applied Physics Letters</i> ; Vol. 63; No. 23; December 6 1993; pp. 3203-3205./Discussed in the specification. |
| <u>DE</u> | AH | K. Mukai et al.; "Self-Formed In _{0.5} Ga _{0.5} As Quantum Dots on GaAs Substrates Emitting at 1.3μm"; <i>Japanese Journal of Applied Physics</i> Vol. 33; Part 2, No. 12A; December 1 1994; pp. L1710-1712./Discussed in the specification. |
| <u>DF</u> | AI | J. Oshinowo et al.; "Highly uniform InGaAs/GaAs quantum dots (~15 nm) by metalorganic chemical vapor deposition"; <i>Applied Physics Letters</i> ; Vol. 65; No. 11; September 12 1994; pp. 1421-1423./Discussed in the specification. |
| Examiner | Date Considered | |
| <u>Barbieri</u> | 5/11/05 | |